BLM7G1822S-40AB; BLM7G1822S-40ABG LDMOS 2-stage power MMIC

AMPLEON

Rev. 2 — 1 September 2015

Product data sheet

Product profile

1.1 General description

The BLM7G1822S-40AB(G) is a dual section, asymmetric, 2-stage power MMIC using Ampleon's state of the art GEN7 LDMOS technology. This multiband device is perfectly suited as small cell final in Doherty configuration, or as general purpose driver in the 1805 MHz to 2170 MHz frequency range. Available in gull wing or straight lead outline.

Table 1. **Performance**

Typical RF performance at $T_{case} = 25 \, ^{\circ}\text{C}$; $I_{Dq1} = 20 \, \text{mA}$; $I_{Dq2} = 76 \, \text{mA}$ for carrier section: $I_{Dq1} = 40$ mA and $I_{Dq2} = 120$ mA for peaking section.

Test signal: 3GPP test model 1; single carrier W-CDMA; 64 DPCH; PAR = 9.9 dB at 0.01% probability on CCDF; per section in a class-AB production circuit.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	η_D	ACPR _{5M}
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
single carrier W-CDMA						
carrier section	2167.5	28	2	31.5	25.5	-37
peaking section	2167.5	28	4	31.5	26.5	-38

1.2 Features and benefits

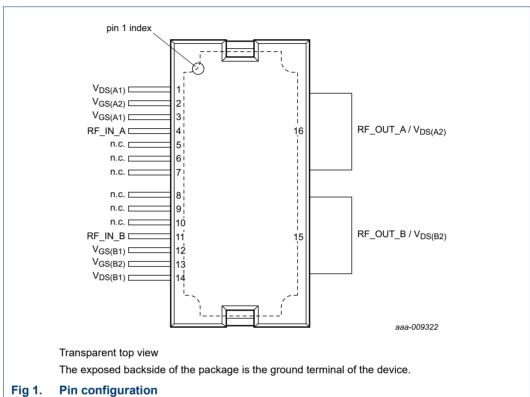
- Designed for broadband operation (frequency 1805 MHz to 2170 MHz)
- High section-to-section isolation enabling multiple combinations
- High Doherty efficiency thanks to 2: 1 asymmetry
- Integrated temperature compensated bias
- Biasing of individual stages is externally accessible
- Integrated ESD protection
- Excellent thermal stability
- High power gain
- On-chip matching for ease of use
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

1.3 Applications

- RF power MMIC for W-CDMA base stations in the 1805 MHz to 2170 MHz frequency range. Possible circuit topologies are the following as also depicted in Section 8.1:
 - Asymmetric final stage in Doherty configuration
 - Asymmetric driver for high power Doherty amplifier

Pinning information 2.

Pinning 2.1



2.2 Pin description

Pin description Table 2.

Symbol	Pin	Description
V _{DS(A1)}	1	drain-source voltage of carrier section, driver stage (A1)
V _{GS(A2)}	2	gate-source voltage of carrier section, final stage (A2)
V _{GS(A1)}	3	gate-source voltage of carrier section, driver stage (A1)
RF_IN_A	4	RF input carrier section (A)
n.c.	5	not connected
n.c.	6	not connected
n.c.	7	not connected
n.c.	8	not connected
n.c.	9	not connected
n.c.	10	not connected
RF_IN_B	11	RF input peaking section (B)
V _{GS(B1)}	12	gate-source voltage of peaking section, driver stage (B1)
V _{GS(B2)}	13	gate-source voltage of peaking section, final stage (B2)
V _{DS(B1)}	14	drain-source voltage of peaking section, driver stage (B1)

Table 2. Pin description ... continued

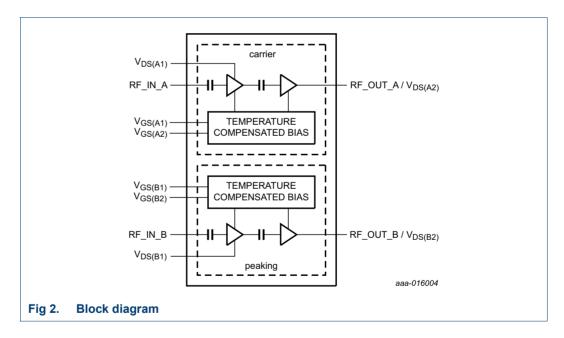
Symbol	Pin	Description
RF_OUT_B/V _{DS(B2)}	15	RF output peaking section (B) / drain-source voltage of peaking section, final stage (B2)
RF_OUT_A/V _{DS(A2)}	16	RF output carrier section (A) / drain-source voltage of carrier section, final stage (A2)
GND	flange	RF ground

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BLM7G1822S-40AB	HSOP16F	plastic, heatsink small outline package; 16 leads (flat)	SOT1211-2			
BLM7G1822S-40ABG	HSOP16	plastic, heatsink small outline package; 16 leads	SOT1212-2			

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C
T _{case}	case temperature		-	150	°C

^[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Value	Unit				
Carrier section									
R _{th(j-c)}	thermal resistance from junction to case	final stage; T _{case} = 90 °C; P _L = 1.78 W	/ <u>[1]</u>		K/W				
		driver stage; T _{case} = 90 °C; P _L = 1.78 W	<u>[1]</u>	12.4	K/W				
Peaking	section								
R _{th(j-c)}	thermal resistance from junction to case	final stage; T _{case} = 90 °C; P _L = 1.26 W	<u>[1]</u>	2.4	K/W				
		driver stage; T _{case} = 90 °C; P _L = 1.26 W	[1]	7.6	K/W				

^[1] When operated with a CW signal.

7. Characteristics

Table 6. DC characteristics

 $T_{\rm case}$ = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Carrier s	ection					
Final stag	e					
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 150.8 \mu\text{A}$	65	-	-	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28 \text{ V}; I_{D} = 76 \text{ mA}$	1.6	2.1	2.6	V
		$V_{DS} = 28 \text{ V}; I_D = 76 \text{ mA}$	1.6	2.65	3.5	V
$\Delta I_{Dq}/\Delta T$	quiescent drain current variation with temperature	$-40 ^{\circ}\text{C} \le T_{case} \le +85 ^{\circ}\text{C}$ [1]	-	±1	-	%
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	V _{GS} = 5.65 V; V _{DS} = 10 V	-	2.8	-	Α
I _{GSS}	gate leakage current	V _{GS} = 1.0 V; V _{DS} = 0 V	-	-	140	nA
Driver sta	ge			'		'
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 30.16 \mu\text{A}$	65	-	-	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 20 mA	1.6	2.15	2.6	V
		$V_{DS} = 28 \text{ V}; I_D = 20 \text{ mA}$ [2]	1.6	2.7	3.5	V
$\Delta I_{Dq}/\Delta T$	quiescent drain current variation with temperature	$-40 ^{\circ}\text{C} \le T_{case} \le +85 ^{\circ}\text{C}$ [2]	-	±1	-	%
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	V _{GS} = 5.65 V; V _{DS} = 10 V	-	0.55	-	Α
I _{GSS}	gate leakage current	V _{GS} = 1.0 V; V _{DS} = 0 V	-	-	140	nA

Table 6. DC characteristics ... continued

 $T_{case} = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Peaking s	section					
Final stag	e					
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 302 \mu\text{A}$	65	-	-	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 120 mA	1.6	2.1	2.6	V
		V _{DS} = 28 V; I _D = 120 mA [3]	1.6	2.65	3.5	V
$\Delta I_{Dq}/\Delta T$	quiescent drain current variation with temperature	-40 °C ≤ T _{case} ≤ +85 °C [3]	-	±1	-	%
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.4	μА
I _{DSX}	drain cut-off current	V _{GS} = 5.65 V; V _{DS} = 10 V	-	5.4	-	Α
I _{GSS}	gate leakage current	V _{GS} = 1.0 V; V _{DS} = 0 V	-	-	140	nA
Driver sta	ge					
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 58 \mu\text{A}$	65	-	-	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 40 mA	1.6	2.15	2.6	V
		$V_{DS} = 28 \text{ V}; I_D = 40 \text{ mA}$	1.6	2.7	3.5	V
$\Delta I_{Dq}/\Delta T$	quiescent drain current variation with temperature	-40 °C ≤ T _{case} ≤ +85 °C [4]	-	±1	-	%
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.4	μА
I _{DSX}	drain cut-off current	V _{GS} = 5.65 V; V _{DS} = 10 V	-	1.04	-	Α
I _{GSS}	gate leakage current	V _{GS} = 1.0 V; V _{DS} = 0 V	-	-	140	nA

- [1] In production circuit with 1105.6 Ω gate feed resistor.
- [2] In production circuit with 765 Ω gate feed resistor.
- [3] In production circuit with 825.6 Ω gate feed resistor.
- [4] In production circuit with 850 Ω gate feed resistor.

Table 7. RF Characteristics

Typical RF performance at $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq1} = 20$ mA (carrier section, driver stage); $I_{Dq2} = 76$ mA (carrier section, final stage); $P_{L(AV)} = 2$ W (carrier section); $I_{Dq1} = 40$ mA (peaking section, driver stage); $I_{Dq2} = 120$ mA (peaking section, final stage); $P_{L(AV)} = 4$ W (peaking section) unless otherwise specified, measured in an Ampleon straight lead production circuit.

Parameter	Conditions	Min	Тур	Max	Unit
ection		-			
ıl: single carrier W-CDMA [1]					
power gain	f = 1807.5 MHz	-	31.8	-	dB
	f = 2167.5 MHz	30	31.5	33	dB
drain efficiency	f = 1807.5 MHz	-	18	-	%
	f = 2167.5 MHz	21	25.5		%
input return loss	f = 2167.5 MHz	-	-15	-10	dB
adjacent channel power ratio (5 MHz)	f = 1807.5 MHz	-	-39	-	dBc
	f = 2167.5 MHz	-	-37	-33	dBc
output peak-to-average ratio	f = 1807.5 MHz	-	8.4	-	dB
	f = 2167.5 MHz	6.4	7.7	-	dB
	power gain drain efficiency input return loss adjacent channel power ratio (5 MHz)	Single carrier W-CDMA [1] power gain f = 1807.5 MHz f = 2167.5 MHz drain efficiency f = 1807.5 MHz f = 2167.5 MHz input return loss f = 2167.5 MHz adjacent channel power ratio (5 MHz) f = 1807.5 MHz output peak-to-average ratio f = 1807.5 MHz	Single carrier W-CDMA [1] F = 1807.5 MHz -	Single carrier W-CDMA [1] F = 1807.5 MHz - 31.8	Single carrier W-CDMA [1] F = 1807.5 MHz

Table 7. RF Characteristics ... continued

Typical RF performance at $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq1} = 20$ mA (carrier section, driver stage); $I_{Dq2} = 76$ mA (carrier section, final stage); $P_{L(AV)} = 2$ W (carrier section); $I_{Dq1} = 40$ mA (peaking section, driver stage); $I_{Dq2} = 120$ mA (peaking section, final stage); $P_{L(AV)} = 4$ W (peaking section) unless otherwise specified, measured in an Ampleon straight lead production circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Peaking s	section					
Test signa	ıl: single carrier W-CDMA [1]					
Gp	power gain	f = 1807.5 MHz	-	31.3	-	dB
		f = 2167.5 MHz	30	31.5	33	dB
η_{D}	drain efficiency	f = 1807.5 MHz	-	25.5	-	%
		f = 2167.5 MHz	22	26.5 -	%	
RLin	input return loss	f = 2167.5 MHz	-	-20	-10	dB
ACPR _{5M}	adjacent channel power ratio (5 MHz)	f = 1807.5 MHz	-	-41	-	dBc
		f = 2167.5 MHz	-	-38	-34	dBc
PARO	output peak-to-average ratio	f = 1807.5 MHz	-	8.2	-	dB
		f = 2167.5 MHz	6.5	7.9	-	dB
Test signa	I: CW [2]		'	,	-	,
$\Delta \phi_{s21}$	phase response difference	normalized; between sections	-10	-	+10	deg
$\Delta s_{21} ^2$	insertion power gain difference	normalized; between sections	-0.5	-	+0.5	dB

^{[1] 3}GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01% probability on CCDF.

8. Application information

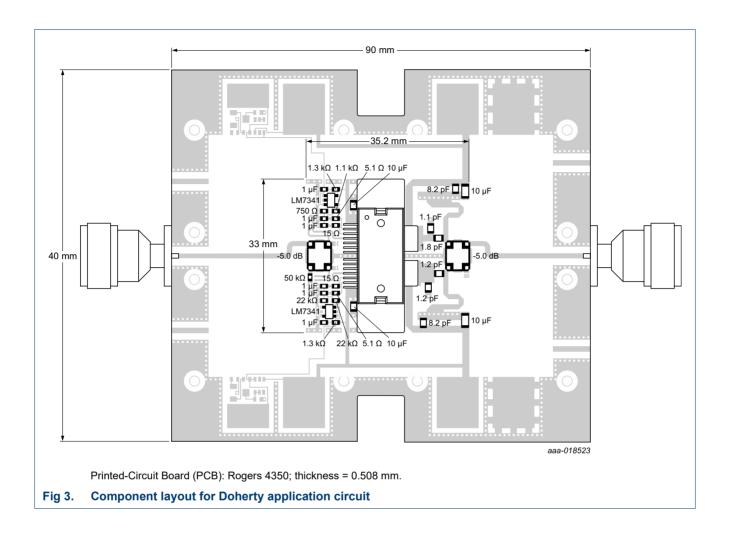
Table 8. Typical performance

 $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq1} = I_{Dq2} = 100$ mA (carrier section, driver and final stages); $V_{GS1} = 2.55$ V (peaking section, driver stage); $V_{GS2} = 1.47$ V (peaking section, final stage); Test signal: 1-C W-CDMA; TM1; 64 DPCH; PAR 9.9dB at 0.01% probability CCDF; in an Ampleon, f = 2110 MHz to 2170 MHz, Doherty application circuit (see Figure 3 and Figure 4).

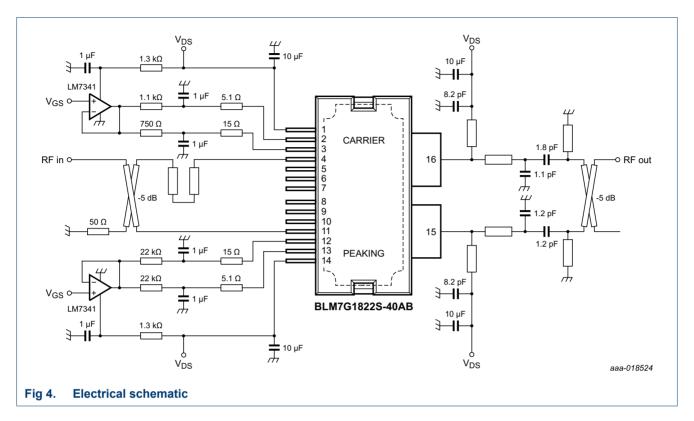
Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
P _{L(3dB)}	output power at 3 dB gain compression	f = 2140 MHz	-		46.6	-	W
η_{D}	drain efficiency	8 dB OBO (P _L = 38.6 dBm); f = 2140 MHz	-		36.5	-	%
Gp	power gain	P _{L(AV)} = 7.25 W; f = 2140 MHz	-		26.1	-	dB
B _{video}	video bandwidth	P _{L(AV)} = 7.25 W; f = 2140 MHz; 2-tone CW	-		145	-	MHz
G _{flat}	gain flatness	P _{L(AV)} = 7.25 W	-		0.2	-	dB
ΔG/ΔT	gain variation with temperature	f = 2140 MHz	[1] _		0.03	-	dB/°C
K	Rollett stability factor	T_{case} = -40 °C; f = 0.1 GHz to 3 GHz	[1] _		>1	-	

^[1] For carrier and peaking sections (S-parameters measured with load-pull jig).

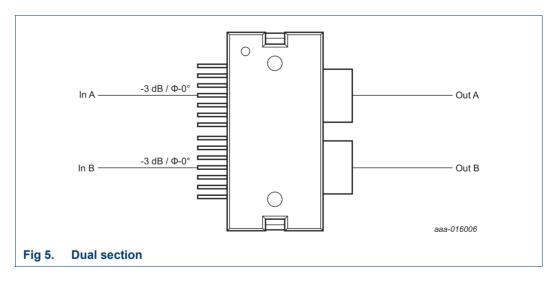
^[2] f = 2170 MHz.

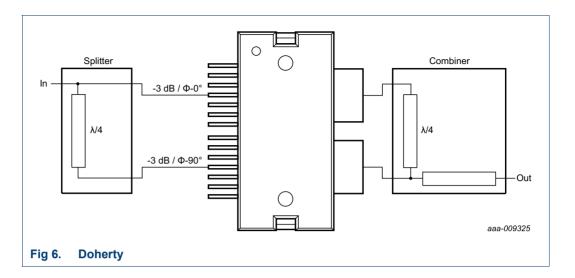


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8.1 Possible circuit topologies





8.2 Ruggedness in class-AB operation

The BLM7G1822S-40AB and BLM7G1822S-40ABG are capable of withstanding a load mismatch corresponding to VSWR = 10:1 through all phases under the following conditions: V_{DS} = 32 V; I_{Dq1} = 20 mA and I_{Dq2} = 75 mA for carrier section; I_{Dq1} = 40 mA and I_{Dq2} = 120 mA for peaking section; P_i is corresponding to $P_{L(3dB)}$ under Z_S = 50 Ω load; f = 2140 MHz.

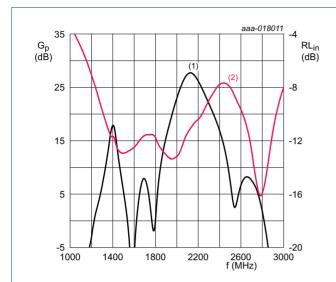
8.3 Impedance information

Table 9. Typical impedance tuned for maximum output power

Measured load-pull data at 3 dB gain compression point; test signal: pulsed CW; $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq1} = 20$ mA (carrier section, driver stage); $I_{Dq2} = 65$ mA (carrier section, final stage); $I_{Dq1} = 40$ mA (peaking section, driver stage); $I_{Dq2} = 130$ mA (carrier section, final stage); $I_{p} = 100$ μs; $\delta = 10$ %; $Z_{S} = 50$ Ω. Typical values unless otherwise specified.

f (MHz)	tuned for max	kimum outp	ut powe	r		tuned for max	tuned for maximum efficiency				
	Z _L	G _{p(max)}	PL	η _{add}	AM-PM	Z _L	G _{p(max)}	PL	η _{add}	AM-PM	
	(Ω)	(dB)	(W)	(%)	(deg)	(Ω)	(dB)	(W)	(%)	(deg)	
carrier	section	'			'						
BLM7G	1822S-40AB										
1700	15.3 – j14.5	33.2	42.7	50.6	8.3	28.5 – j20.2	34.6	41.6	56.5	9.2	
1800	16.3 – j11.7	32.9	42.7	50.8	6.3	31.3 – j8.60	34.1	41.6	57.1	7.0	
1900	16.1 – j9.70	32.1	42.8	50.8	6.1	26.5 - j0.01	33.3	41.7	57.3	6.9	
2000	15.5 – j8.10	31.5	42.8	50.1	6.1	21.0 + j2.20	32.6	42.0	56.4	7.3	
2100	14.4 – j6.90	31.5	42.9	50.0	6.9	15.6 + j2.00	32.9	42.1	55.8	8.6	
2200	13.7 – j6.60	31.7	42.7	49.8	8.5	12.3 + j1.20	33.0	41.6	54.3	9.6	
2300	12.8 – j6.80	31.4	42.5	49.1	10.6	10.0 + j0.10	32.5	41.3	53.6	10.3	
BLM7G	1822S-40ABG			1	1			1	1		
1700	15.8 – j16.1	33.5	42.5	52.9	9.2	28.9 – j21.8	35.1	41.6	57.9	11.1	
1800	16.5 – j13.8	32.9	42.5	51.2	7.7	30.6 – j11.6	34.3	41.6	56.8	8.4	
1900	16.7 – j12.4	32.2	42.5	50.2	7.2	27.9 – j4.64	33.5	41.7	55.9	7.8	
2000	16.3 – j9.74	31.7	42.5	51.2	7.3	20.4 + j0.45	32.7	41.7	55.6	9.0	
2100	15.6 – j8.61	31.5	42.6	52.0	9.5	15.9 + j0.68	32.6	41.7	56.4	11.8	
2200	14.6 – j8.87	31.3	42.5	49.7	10.3	12.7 – j0.44	32.4	41.6	53.8	12.1	
2300	13.4 – j9.32	30.5	42.4	48.2	12.8	10.7 – j1.98	31.7	41.6	53.7	13.2	
peaking	g section	'								-	
BLM7G	1822S-40AB										
1700	7.02 – j10.1	33.4	45.4	51.2	1.0	13.6 – j11.6	34.7	44.1	56.4	3.9	
1800	7.10 – j9.70	33.3	45.5	50.5	0.9	13.4 – j7.20	34.4	44.3	57.2	2.9	
1900	6.90 - j10.0	32.6	45.6	48.8	-0.1	11.6 – j5.20	33.6	44.4	56.7	2.2	
2000	6.68 - j10.2	32.6	45.6	49.4	-0.5	9.30 - j4.80	33.5	44.5	56.1	2.1	
2100	6.52 – j10.2	33.3	45.6	49.3	4.1	7.20 – j5.40	33.9	44.5	54.9	6.4	
2200	6.39 – j10.4	33.1	45.4	49.5	7.5	6.20 - j6.30	33.8	44.5	54.6	8.5	
2300	5.83 – j10.5	31.5	45.1	50.2	11.2	5.50 - j7.50	32.4	44.4	54.5	12.2	
BLM7G	1822S-40ABG	1		1	1	l	1	1	1	1	
1700	6.43 – j11.5	32.5	45.4	53.9	1.9	13.8 – j13.4	33.9	44.0	61.0	3.2	
1800	6.54 – j11.8	32.3	45.4	52.5	1.2	14.5 – j10.0	33.7	44.2	59.4	2.8	
1900	6.59 – j12.2	32.3	45.5	51.8	-6	13.0 – j8.07	33.5	44.3	58.9	2.4	
2000	6.49 – j12.1	32.5	45.5	51.3	-1.7	9.21 – j7.30	33.6	44.5	57.2	1.2	
2100	6.48 – j12.1	32.7	45.6	50.7	3.4	7.36 – j7.91	33.6	44.6	57.1	2.4	
2200	6.12 – j12.4	32.6	45.3	51.2	8.2	6.21 – j8.66	33.5	44.4	56.8	7.5	
2300	5.78 – j12.4	31.8	45.0	52.0	10.9	5.34 – j9.17	32.5	44.2	56.7	11.5	

8.4 Graphs

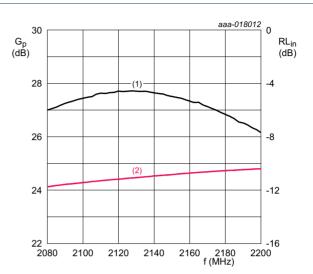


 T_{case} = 25 °C; V_{DS} = 28 V; P_L = 6.3 W; I_{Dq1} = I_{Dq2} = 100 mA (carrier section, driver and final

 V_{GS1} = 2.55 V (peaking section, driver stage); V_{GS2} = 1.47 V (peaking section, final stage). Test signal: CW

- (1) magnitude of G_p
- (2) magnitude of RLin

Fig 7. Wideband power gain and input return loss as function of frequency; typical values



 $\rm T_{case}$ = 25 °C; $\rm V_{DS}$ = 28 V; $\rm P_L$ = 6.3 W; $\rm I_{Dq1}$ = $\rm I_{Dq2}$ = 100 mA (carrier section, driver and final stages);

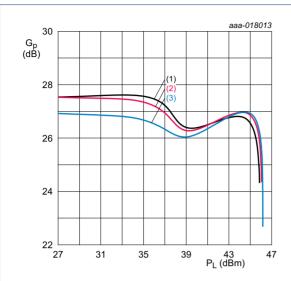
 V_{GS1} = 2.55 V (peaking section, driver stage); V_{GS2} = 1.47 V (peaking section, final stage). Test signal: CW

- (1) magnitude of G_p
- (2) magnitude of RLin

Fig 8. In-band power gain and input return loss as function of frequency; typical values

BLM7G1822S-40AB(G)

LDMOS 2-stage power MMIC



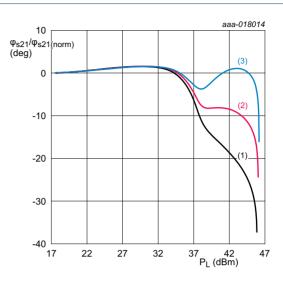
 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = I_{Dq2} = 100 mA (carrier section, driver and final stages);

 V_{GS1} = 2.55 V (peaking section, driver stage); V_{GS2} = 1.47 V (peaking section, final stage).

Test signal: CW

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

Fig 9. Power gain as a function of output power; typical values



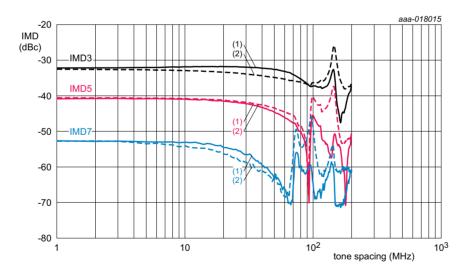
 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = I_{Dq2} = 100 mA (carrier section, driver and final stages);

 V_{GS1} = 2.55 V (peaking section, driver stage); V_{GS2} = 1.47 V (peaking section, final stage).

Test signal: CW

- (1) f = 2110 MHz
- (2) f = 2140 MHz
- (3) f = 2170 MHz

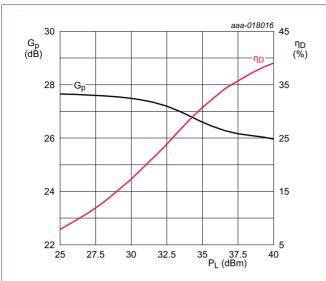
Fig 10. Normalized phase response as a function of output power; typical values



 $T_{case} = 25 \, ^{\circ}\text{C}$; $V_{DS} = 28 \, ^{\circ}\text{V}$; $I_{Dq1} = I_{Dq2} = 100 \, \text{mA}$ (carrier section, driver and final stages); $V_{GS1} = 2.55 \, ^{\circ}\text{V}$ (peaking section, driver stage); $V_{GS2} = 1.47 \, ^{\circ}\text{V}$ (peaking section, final stage). Test signal: 2-tone CW; $f_c = 2140 \, \text{MHz}$.

- (1) IMD low
- (2) IMD high

Fig 11. Intermodulation distortion as a function of tone spacing; typical values



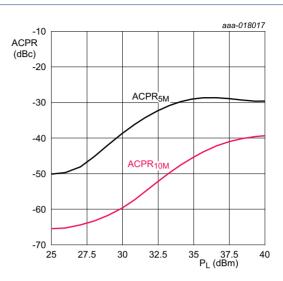
 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = I_{Dq2} = 100 mA (carrier section, driver and final stages);

V_{GS1} = 2.55 V (peaking section, driver stage);

V_{GS2} = 1.47 V (peaking section, final stage).

Test signal: 1-carrier W-CDMA; test model 1; 64 DPCH; PAR 9.9 dB at 0.01% probability CCDF; f = 2140 MHz.

Fig 12. Power gain and drain efficiency as function of output power; typical values



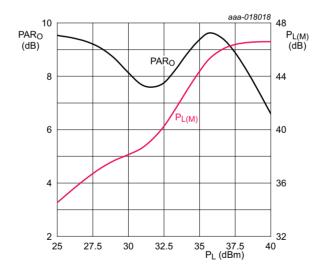
 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = I_{Dq2} = 100 mA (carrier section, driver and final stages);

V_{GS1} = 2.55 V (peaking section, driver stage);

V_{GS2} = 1.47 V (peaking section, final stage).

Test signal: 1-carrier W-CDMA; test model 1; 64 DPCH; PAR 9.9 dB at 0.01% probability CCDF; f = 2140 MHz.

Fig 13. Adjacent channel power ratio as a function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} = I_{Dq2} = 100 mA (carrier section, driver and final stages); V_{GS1} = 2.55 V (peaking section, driver stage); V_{GS2} = 1.47 V (peaking section, final stage).

Test signal: 1-carrier W-CDMA; test model 1; 64 DPCH; PAR 9.9 dB at 0.01% probability CCDF; f = 2140 MHz.

Fig 14. Output peak-to-average ratio and peak output power as function of output power; typical values

9. Package outline

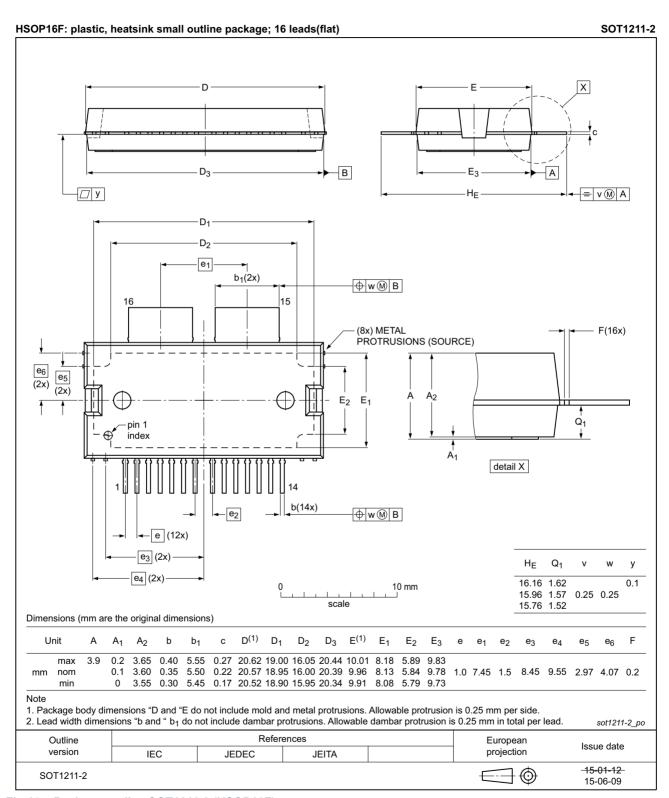


Fig 15. Package outline SOT1211-2 (HSOP16F)

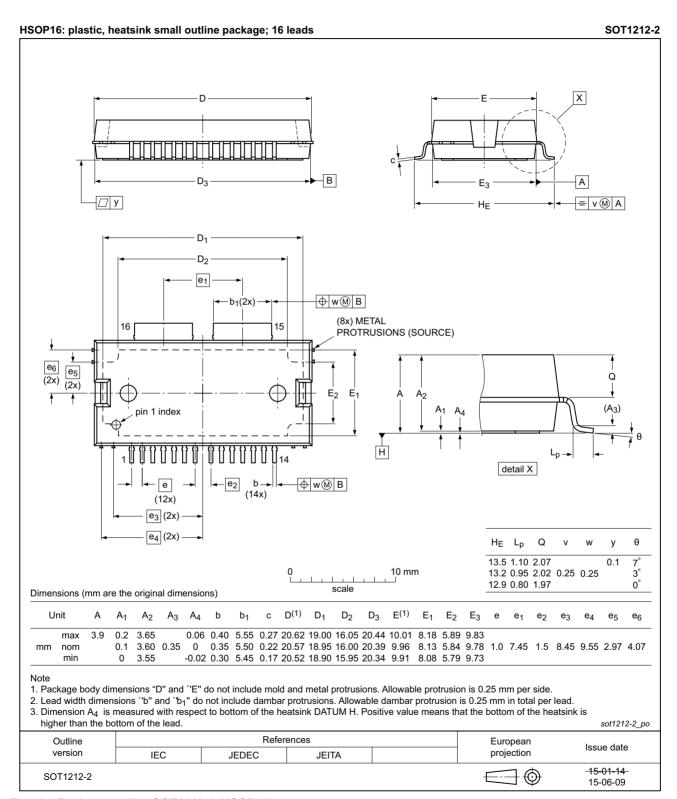


Fig 16. Package outline SOT1212-2 (HSOP16)

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

11. Abbreviations

Table 10. Abbreviations

Acronym	Description			
AM	Amplitude Modulation			
3GPP	3rd Generation Partnership Project			
CCDF	Complementary Cumulative Distribution Function			
CW	Continuous Wave			
DPCH	Dedicated Physical CHannel			
ESD	ElectroStatic Discharge			
GEN7	Seventh Generation			
LDMOS	Laterally Diffused Metal Oxide Semiconductor			
MMIC	Monolithic Microwave Integrated Circuit			
MTF	Median Time to Failure			
ОВО	Output Back Off			
PAR	Peak-to-Average Ratio			
PM	Phase Modulation			
VSWR	Voltage Standing-Wave Ratio			
W-CDMA	Wideband Code Division Multiple Access			

12. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BLM7G1822S-40AB_S-40ABG#2	20150901	Product data sheet		BLM7G1822S-40AB_S -40ABG v.1		
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. Legal texts have been adapted to the new company name where appropriate. 					
BLM7G1822S-40AB S-40ABG v.1	20150710	Product data sheet	-	-		

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13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

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BLM7G1822S-40AB S-40ABG#2

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BLM7G1822S-40AB(G)

LDMOS 2-stage power MMIC

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BLM7G1822S-40AB(G)

LDMOS 2-stage power MMIC

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